Xin Chen

List of Publications by Year
in descending order

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21	388	1039880 9	752573 20
papers	citations	h-index	g-index

21	21	21	333
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Quasi-phase matched second harmonic generation in a PMN-38PT crystal. Optics Letters, 2022, 47, 2056.	1.7	4
2	Optical Induction and Erasure of Ferroelectric Domains in Tetragonal PMNâ€38PT Crystals. Advanced Optical Materials, 2022, 10, 2102115.	3.6	10
3	Nonlinear detour phase holography. Nanoscale, 2021, 13, 2693-2702.	2.8	11
4	Localized Ferroelectric Domains via Laser Poling in Monodomain Calcium Barium Niobate Crystal. Laser and Photonics Reviews, 2021, 15, 2100088.	4.4	11
5	Nonlinear Optical Effects at Ferroelectric Domain Walls. , 2018, , .		0
6	Broadband enhancement of ÄŒerenkov second harmonic generation in a sunflower spiral nonlinear photonic crystal. Optics Express, 2018, 26, 8628.	1.7	10
7	Three-dimensional nonlinear photonic crystal in ferroelectric barium calcium titanate. Nature Photonics, 2018, 12, 591-595.	15.6	135
8	Enhanced fourth harmonic generation via nonlinear ÄŒerenkov interaction in periodically poled lithium niobate crystal. Optics Express, 2016, 24, 29948.	1.7	5
9	Quasi-phase matching via femtosecond laser-induced domain inversion in lithium niobate waveguides. Optics Letters, 2016, 41, 2410.	1.7	46
10	Ferroelectric domain engineering by focused infrared femtosecond pulses. Applied Physics Letters, 2015, 107, .	1.5	74
11	Nonlinear diffraction in orientation-patterned semiconductors. Optics Express, 2015, 23, 14903.	1.7	10
12	Calcium barium niobate as a functional material for broadband optical frequency conversion. Optics Letters, 2014, 39, 1330.	1.7	7
13	Highly ordered GaN-based nanowire arrays grown on patterned (100) silicon and their optical properties. Chemical Communications, 2014, 50, 682-684.	2.2	25
14	Enhanced performances of InGaN/GaN-based blue light-emitting diode with InGaN/AlInGaN superlattice electron blocking layer. Chinese Physics B, 2014, 23, 068502.	0.7	4
15	Droop improvement in blue InGaN light-emitting diodes with GaN/InGaN superlattice barriers. Chinese Physics B, 2013, 22, 068505.	0.7	5
16	Enhanced performance of InGaN/GaN based solar cells with an In_005Ga_095N ultra-thin inserting layer between GaN barrier and In_02Ga_08N well. Optics Express, 2013, 21, 7118.	1.7	9
17	Enhanced performance of InGaN/GaN multiple quantum well solar cells with double indium content. Chinese Physics B, 2013, 22, 088401.	0.7	2
18	Efficiency and droop improvement in a blue InGaN-based light emitting diode with a p-InGaN layer inserted in the GaN barriers. Chinese Physics B, 2013, 22, 098504.	0.7	1

#	Article	IF	Citations
19	Advantages of an InGaN-based light emitting diode with a p-InGaN/p-GaN superlattice hole accumulation layer. Chinese Physics B, 2013, 22, 058502.	0.7	5
20	Advantages of InGaN/GaN multiple quantum well solar cells with stepped-thickness quantum wells. Chinese Physics B, 2013, 22, 078402.	0.7	2
21	Efficiency enhancement of InGaN based blue light emitting diodes with InGaN/GaN multilayer barriers. Chinese Physics B, 2012, 21, 118502.	0.7	12